MSKSEMI















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FEATURES

- High Collector Current
- Complementary to PXT8550

SOT-89

1. BASE



3. EMITTER

MAXIMUM RATINGS (Ta=25℃ unless otherwise noted)

Symbol	Parameter Value		Unit
V _{СВО}	Collector-Base Voltage	40	V
V _{CEO}	Collector-Emitter Voltage	25	V
V _{EBO}	Emitter-Base Voltage	5	V
Ic	Collector Current -Continuous	1.5	Α
Pc	Collector Power Dissipation	0.5	W
R _{OJA}	Thermal Resistance From Junction To Ambient	250 °C/W	
TJ	Junction Temperature	150 ℃	
T _{stg}	Storage Temperature	-55~150 ℃	

ELECTRICAL CHARACTERISTICS (Tamb=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	V _{(BR)CBO}	I _C = 100μA, I _E =0	40			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C = 1mA, I _B =0	25			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =100μA, I _C =0	5			V
Collector cut-off current	I _{CBO}	V _{CB} =40V, I _E =0			0.1	μA
Emitter cut-off current	I _{EBO}	V _{EB} = 5V, I _C =0			0.1	μA
DC aureant rain	h _{FE(1)}	V _{CE} =1V, I _C = 100mA	120		400	
DC current gain	h _{FE(2)}	V _{CE} =1V, I _C = 800mA	40			
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =800mA, I _B = 80mA			0.5	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C =800mA, I _B = 80mA			1.2	V
Transition frequency	f⊤	V _{CE} =10V, I _C = 50mA f=30MHz	100			MHz

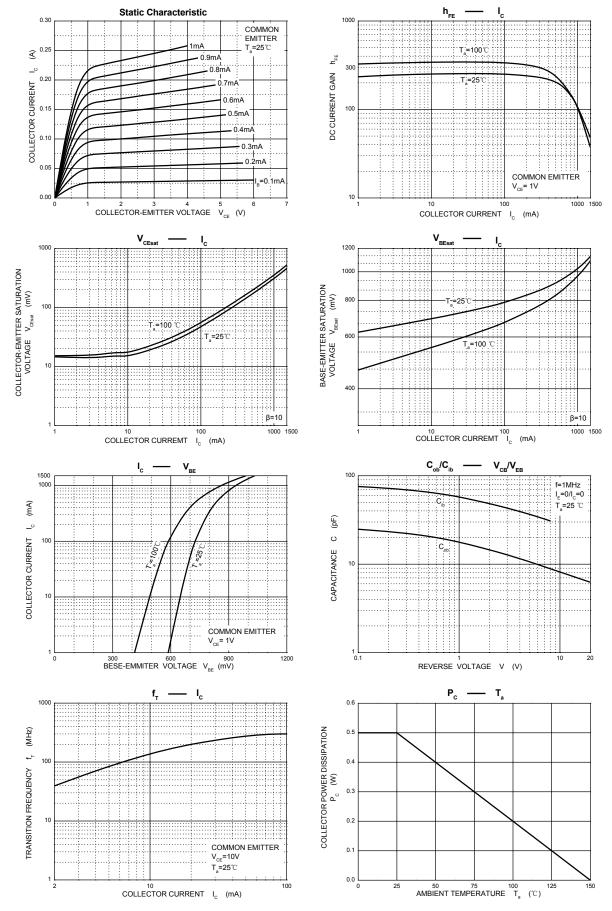
CLASSIFICATION OF hfe(1)

Rank	L	Н	J
Range	120-200	200-350	300-400



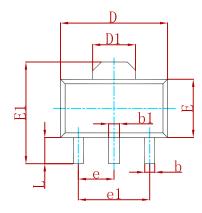


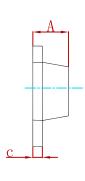
Typical Characteristics





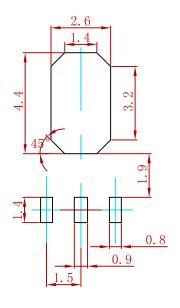
PACKAGE MECHANICAL DATA





Symbol	Dimensions In Millimeters		Dimensions In Inches		
Symbol	Min	Max	Min	Max	
Α	1.400	1.600	0.055	0.063	
b	0.320	0.520	0.013	0.020	
b1	0.400	0.580	0.016	0.023	
С	0.350	0.440	0.014	0.017	
D	4.400	4.600	0.173	0.181	
D1	1.550	REF.	0.061	REF.	
E	2.300	2.600	0.091	0.102	
E1	3.940	4.250	0.155	0.167	
е	1.500 TYP.		0.060 TYP.		
e1	3.000 TYP.		0.118 TYP.		
L	0.900	1.200	0.035	0.047	

Suggested Pad Layout



Note:

- 1.Controlling dimension:in millimeters.
- 2.General tolerance:±0.05mm.
- 3. The pad layout is for reference purposes only.

REEL SPECIFICATION

P/N	PKG	QTY
PXT8050	SOT-89	1000





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